

**Inchange Semiconductor**

**Product Specification**

**Silicon NPN Power Transistors**

**2SC2556 2SC2556A**

**DESCRIPTION**

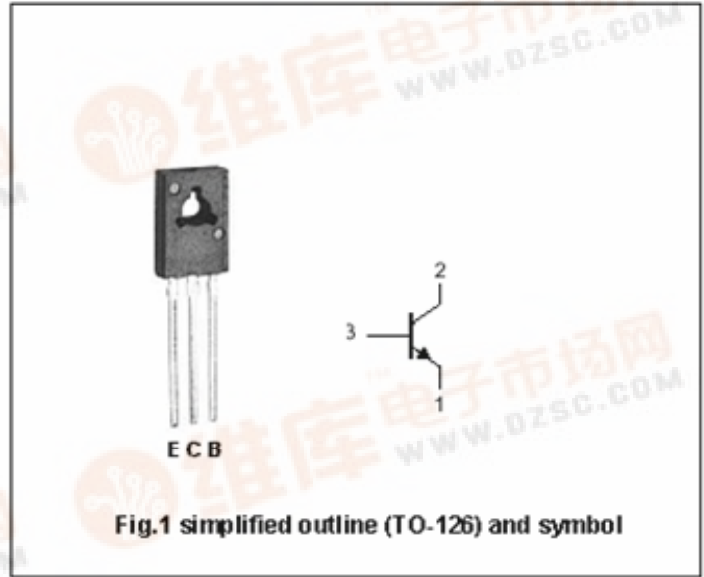
- With TO-126 package
- High  $V_{CBO}$
- Low collector saturation voltage
- High transition frequency

**APPLICATIONS**

- Audio frequency output amplifier

**PINNING**

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



**Absolute maximum ratings( $T_a=25$  )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	2SC2556	130	V
		2SC2556A	180	
$V_{CEO}$	Collector- emitter voltage	2SC2556	40	V
		2SC2556A	50	
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		1	A
$I_{CM}$	Collector current-peak		1.5	A
$P_C$	Collector power dissipation	$T_C=25$	1.2	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55 ~ +150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	2SC2556	I <sub>C</sub> =2mA ; I <sub>B</sub> =0	40			V
		2SC2556A		50			
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	2SC2556	I <sub>C</sub> =10 μ A ; I <sub>E</sub> =0	130			V
		2SC2556A		180			
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage		I <sub>E</sub> =10 μ A ; I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage		I <sub>C</sub> =500mA ; I <sub>B</sub> =50mA			0.5	V
I <sub>CBO</sub>	Collector cut-off current		V <sub>CB</sub> =120V ; I <sub>E</sub> =0			0.1	μ A
h <sub>FE-1</sub>	DC current gain		I <sub>C</sub> =1A ; V <sub>CE</sub> =0.5V	150		350	
h <sub>FE-2</sub>	DC current gain		I <sub>C</sub> =0.5A ; V <sub>CE</sub> =2V	150			
C <sub>OB</sub>	Output capacitance		I <sub>E</sub> =0 ; V <sub>CB</sub> =20V ; f=1MHz			30	pF
f <sub>T</sub>	Transition frequency		I <sub>C</sub> =50mA ; V <sub>CE</sub> =10V		200		MHz

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PACKAGE OUTLINE

